

Crystal Interface Lab. Seminar Series

Institute of Engineering Innovation The University of Tokyo

Interfacial Reconstruction and Formation of 2D Electron-Gas at Oxide Interfaces



Department of Condensed Matter Physics Brookhaven National Laboratory Long Island, NY 11973 USA

Abstract

High mobility conduction at the interface of two dissimilar materials and the ability to manipulate the carrier density and mobility of the interfacial charge by electrostatic gating have lead to many fascinating phenomena in the past decade. In this presentation I will give an overview of our recent work on interfacial reconstruction and formation of twodimensional electron-gas in strongly-correlated multilayer oxides investigated by means of high-resolution electron microscopy, electron energy-loss spectroscopy, electron holography, and DC electrical transport measurements. Focus will be on the interfacial electronic structure and charge transfer that are related atomic scale oxygen-hole depletion, valence-state variation, chemical diffusion, and interfacial strain. Examples include SrTiO₃/RO/SrTiO₃ (R=La, Pr, Nd, Sm, Y) and (LaMnO₃)₂₀/(SrMnO₃)₀ superlattices as well as Heusler alloy (Co₂MnSi and Co₂FeSi)-SrTiO₃ interfaces and YBa₂Cu₃O_{7-x}-Pr_{0.68}Ca_{0.32}MnO₃ interfaces. The impact of interfacial charge transfer on competing ferroelectric and ferromagnetic metal-insulator transition, superconductivity order, and other magnetoelectric properties will be discussed. The work was supported by US DOE/BES, under Contract No. DE-AC02-98CH10886.

August 21 (Wed), 2013 10:30 -12:00 Main meeting room at Institute of Engineering Innovation, UT (工学部総合研究機構 9号館1階 大会議室) Organizer: Prof. Yuichi Ikuhara